



FEMTOCLOCKS™ CRYSTAL-TO-3.3V, 2.5V LVPECL CLOCK GENERATOR

ICS843023I

GENERAL DESCRIPTION



The ICS843023I is a Gigabit Ethernet Clock Generator and a member of the HiPerClocks™ family of high performance devices from IDT. The ICS843023I uses a 25MHz crystal to synthesize 250MHz. The ICS843023I has excellent phase jitter performance, over the 1.875MHz – 20MHz integration range. The ICS843023I is packaged in a small 8-pin TSSOP, making it ideal for use in systems with limited board space.

FEATURES

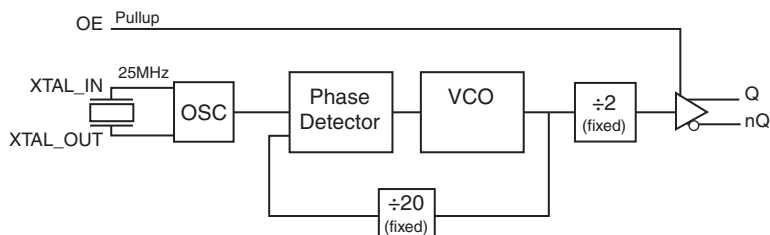
- One differential 3.3V or 2.5V LVPECL output
- Crystal oscillator interface designed for 25MHz, 18pF parallel resonant crystal
- Output frequency range: 240MHz - 320MHz
- VCO range: 480MHz - 640MHz
- RMS phase jitter @ 250MHz, using a 25MHz crystal (1.875MHz - 20MHz): 0.39ps (typical)

Phase noise:

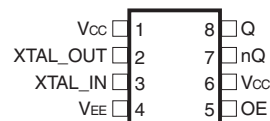
Offset	Noise Power
100Hz	-86.3 dBc/Hz
1kHz	-114.6 dBc/Hz
10kHz	-125.6 dBc/Hz
100kHz	-126.0 dBc/Hz

- Full 3.3V and 2.5V operating supply
- -40°C to 85°C ambient operating temperature
- Available in both standard (RoHS 5) and lead-free (RoHS 6) packages

BLOCK DIAGRAM



PIN ASSIGNMENT



ICS843023I

8-Lead TSSOP

4.40mm x 3.0mm x 0.925mm package body

G Package

Top View

TABLE 1. PIN DESCRIPTIONS

Number	Name	Type		Description
1, 6	V _{CC}	Power		Core supply pin.
2, 3	XTAL_OUT, XTAL_IN	Input		Crystal oscillator interface. XTAL_IN is the input, XTAL_OUT is the output.
4	V _{EE}	Power		Negative supply pin.
5	OE	Input	Pullup	Active high output enable. When logic HIGH, the outputs are enabled and active. When logic LOW, the outputs are disabled and the device is in power down mode. LVCMOS/LVTTL interface levels.
7, 8	nQ, Q	Output		Differential clock outputs. LVPECL interface levels.

Pullup refers to internal input resistors. See Table 2, Pin Characteristics, for typical values.

TABLE 2. PIN CHARACTERISTICS

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
C _{IN}	Input Capacitance			4		pF
R _{PULLUP}	Input Pullup Resistor			51		kΩ

ABSOLUTE MAXIMUM RATINGS

Supply Voltage, V_{CC}	4.6V
Inputs, V_I	-0.5V to $V_{CC} + 0.5V$
Outputs, I_O	
Continuous Current	50mA
Surge Current	100mA
Package Thermal Impedance, θ_{JA}	101.7°C/W (0 mps)
Storage Temperature, T_{STG}	-65°C to 150°C

NOTE: Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

TABLE 3A. POWER SUPPLY DC CHARACTERISTICS, $V_{CC} = 3.3V \pm 5\%$, $T_A = -40^\circ\text{C}$ TO 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{CC}	Core Supply Voltage		3.135	3.3	3.465	V
V_{CCA}	Analog Supply Voltage		3.135	3.3	3.465	V
I_{EE}	Power Supply Current				75	mA

TABLE 3B. POWER SUPPLY DC CHARACTERISTICS, $V_{CC} = 2.5V \pm 5\%$, $T_A = -40^\circ\text{C}$ TO 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{CC}	Core Supply Voltage		2.375	2.5	2.625	V
V_{CCA}	Analog Supply Voltage		2.375	2.5	2.625	V
I_{EE}	Power Supply Current				70	mA

TABLE 3C. LVCMOS/LVTTL DC CHARACTERISTICS, $V_{CC} = 3.3V \pm 5\%$ OR $2.5V \pm 5\%$, $T_A = -40^\circ\text{C}$ TO 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{IH}	Input High Voltage	$V_{CC} = 3.3V$	2		$V_{CC} + 0.3$	V
		$V_{CC} = 2.5V$	1.7		$V_{CC} + 0.3$	V
V_{IL}	Input Low Voltage	$V_{CC} = 3.3V$	-0.3		0.8	V
		$V_{CC} = 2.5V$	-0.3		0.7	V
I_{IH}	Input High Current	OE $V_{CC} = V_{IN} = 3.465V$ or $2.625V$			5	μA
I_{IL}	Input Low Current	OE $V_{CC} = 3.465V$ or $2.625V$, $V_{IN} = 0V$	-150			μA

TABLE 3D. LVPECL DC CHARACTERISTICS, $V_{CC} = 3.3V \pm 5\%$ OR $2.5V \pm 5\%$, $T_A = -40^\circ\text{C}$ TO 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{OH}	Output High Voltage; NOTE 1		$V_{CC} - 1.4$		$V_{CC} - 0.9$	V
V_{OL}	Output Low Voltage; NOTE 1		$V_{CC} - 2.0$		$V_{CC} - 1.7$	V
V_{SWING}	Peak-to-Peak Output Voltage Swing		0.6		1.0	V

NOTE 1: Outputs terminated with 50Ω to $V_{CC} - 2V$.

TABLE 4. CRYSTAL CHARACTERISTICS

Parameter	Test Conditions	Minimum	Typical	Maximum	Units
Mode of Oscillation		Fundamental			
Frequency		24		32	MHz
Equivalent Series Resistance (ESR)				50	Ω
Shunt Capacitance				7	pF
Drive Level				1	mW

TABLE 5A. AC CHARACTERISTICS, $V_{CC} = 3.3V \pm 5\%$, $T_A = -40^\circ\text{C}$ TO 85°C

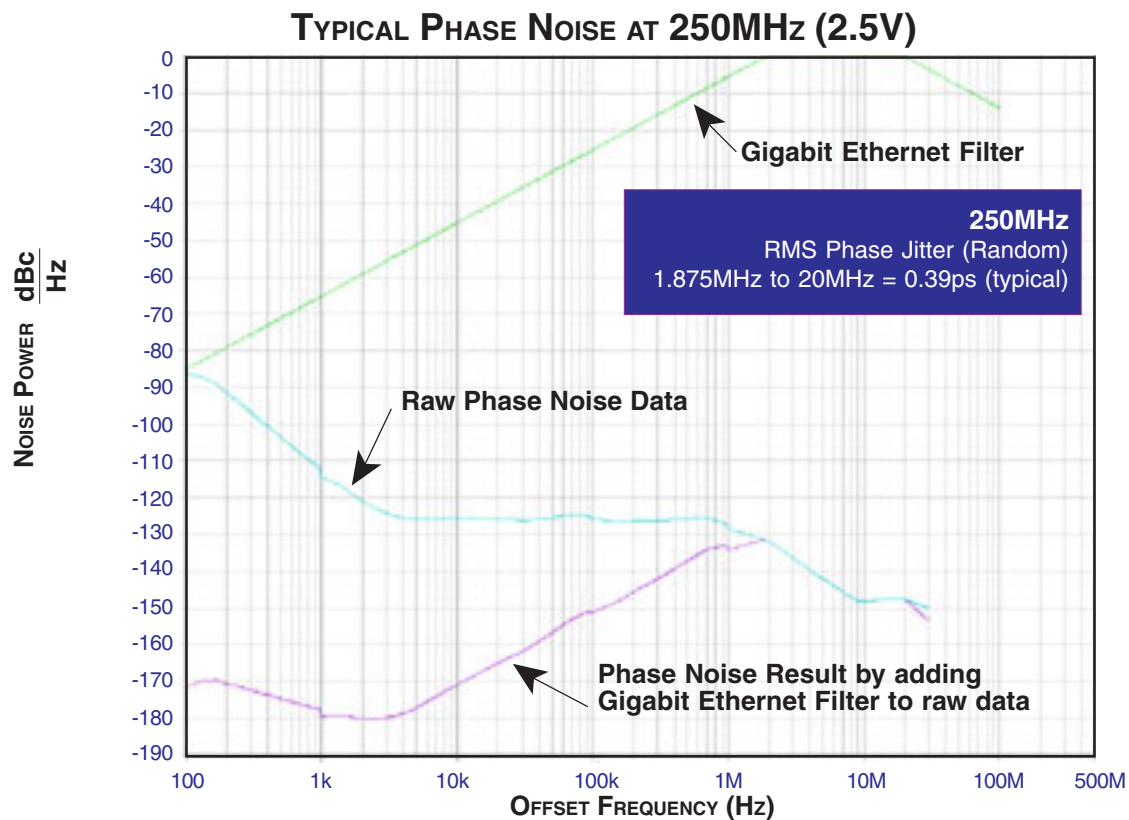
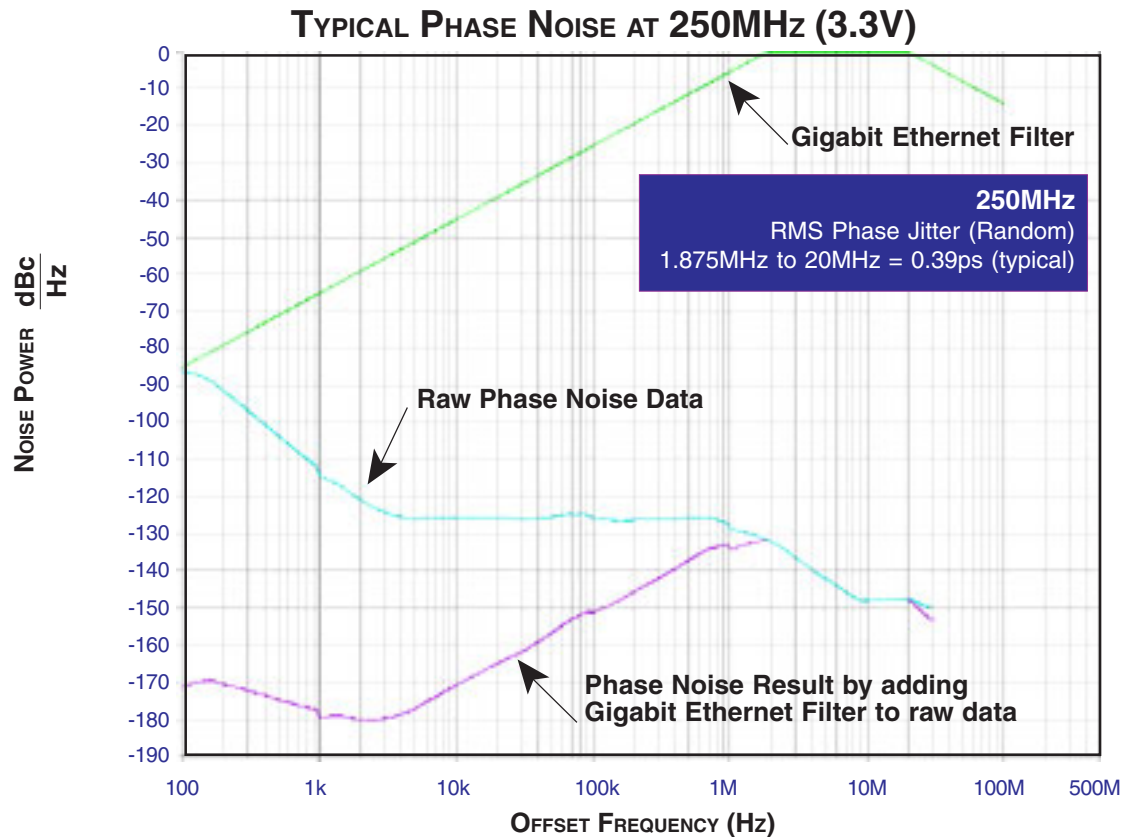
Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
f_{OUT}	Output Frequency		240		320	MHz
$f_{jit}(\emptyset)$	RMS Phase Jitter (Random); NOTE 1	250MHz, Integration Range: 1.875MHz - 20MHz		0.39		ps
t_R / t_F	Output Rise/Fall Time	20% to 80%	300		600	ps
odc	Output Duty Cycle		47		53	%

NOTE 1: Please refer to the Phase Noise Plot after this section.

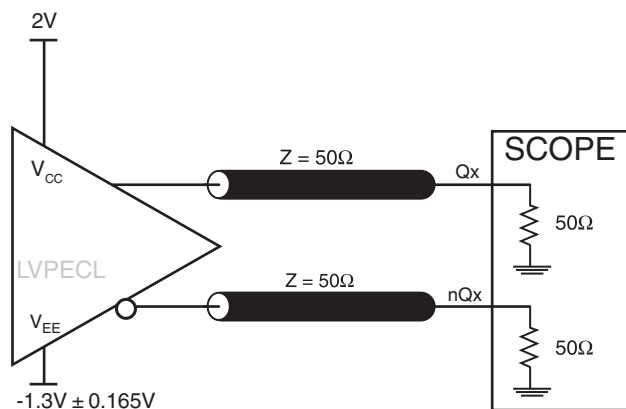
TABLE 5B. AC CHARACTERISTICS, $V_{CC} = 2.5V \pm 5\%$, $T_A = -40^\circ\text{C}$ TO 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
f_{OUT}	Output Frequency		240		320	MHz
$f_{jit}(\emptyset)$	RMS Phase Jitter (Random); NOTE 1	250MHz, Integration Range: 1.875MHz - 20MHz		0.39		ps
t_R / t_F	Output Rise/Fall Time	20% to 80%	300		600	ps
odc	Output Duty Cycle		47		53	%

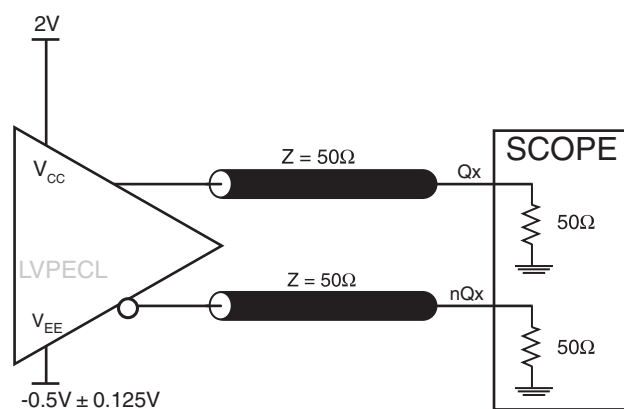
NOTE 1: Please refer to the Phase Noise Plot after this section.



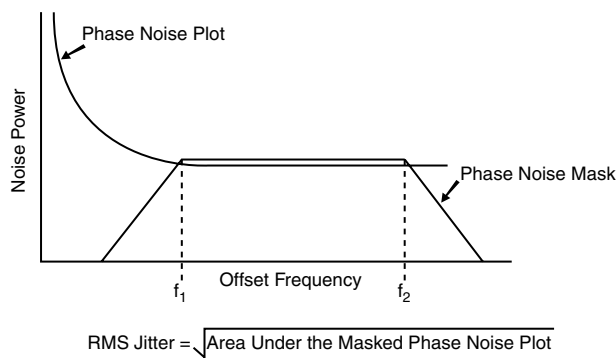
PARAMETER MEASUREMENT INFORMATION



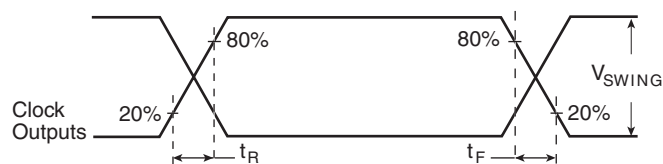
3.3V OUTPUT LOAD AC TEST CIRCUIT



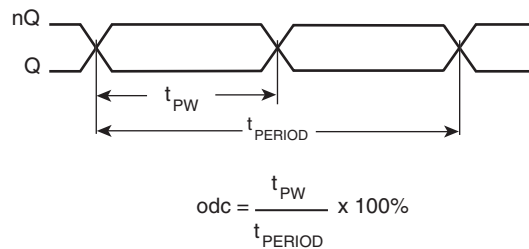
2.5V OUTPUT LOAD AC TEST CIRCUIT



OUTPUT DUTY CYCLE/PULSE WIDTH/PERIOD



OUTPUT RISE/FALL TIME



OUTPUT DUTY CYCLE/PULSE WIDTH/PERIOD

APPLICATION INFORMATION

CRYSTAL INPUT INTERFACE

The ICS843023I has been characterized with 18pF parallel resonant crystals. The capacitor values, C1 and C2, shown in *Figure 1* below were determined using a 25MHz, 18pF parallel

resonant crystal and were chosen to minimize the ppm error. The optimum C1 and C2 values can be slightly adjusted for different board layouts.

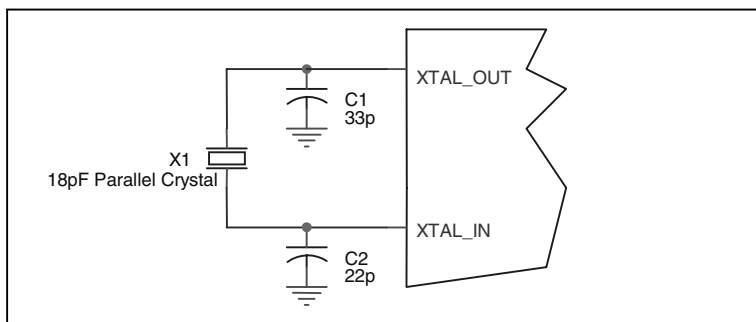


FIGURE 1. CRYSTAL INPUT INTERFACE

LVC MOS TO XTAL INTERFACE

The XTAL_IN input can accept a single-ended LVC MOS signal through an AC couple capacitor. A general interface diagram is shown in *Figure 2*. The XTAL_OUT pin can be left floating. The input edge rate can be as slow as 10ns. For LVC MOS inputs, it is recommended that the amplitude be reduced from full swing to half swing in order to prevent signal interference with the power rail and to reduce noise. This configuration requires that the output impedance of the driver

(R_o) plus the series resistance (R_s) equals the transmission line impedance. In addition, matched termination at the crystal input will attenuate the signal in half. This can be done in one of two ways. First, R_1 and R_2 in parallel should equal the transmission line impedance. For most 50Ω applications, R_1 and R_2 can be 100Ω. This can also be accomplished by removing R_1 and making R_2 50Ω.

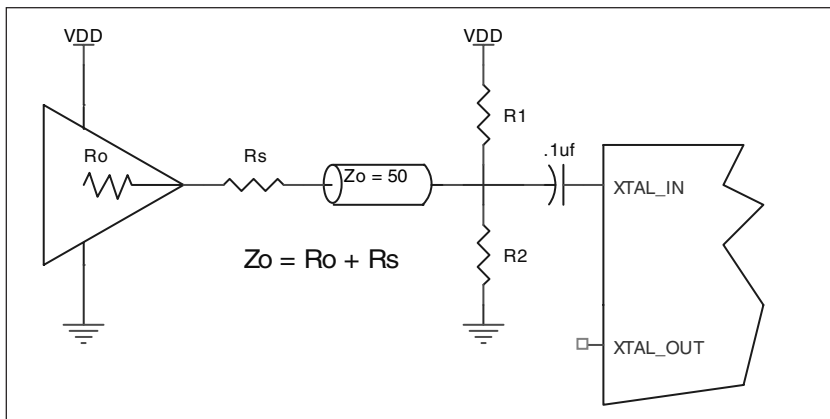


FIGURE 2. General Diagram for LVC MOS Driver to XTAL Input Interface

TERMINATION FOR 3.3V LVPECL OUTPUT

The clock layout topology shown below is a typical termination for LVPECL outputs. The two different layouts mentioned are recommended only as guidelines.

FOUT and nFOUT are low impedance follower outputs that generate ECL/LVPECL compatible outputs. Therefore, terminating resistors (DC current path to ground) or current sources must be used for functionality. These outputs are

designed to drive 50Ω transmission lines. Matched impedance techniques should be used to maximize operating frequency and minimize signal distortion. *Figures 3A and 3B* show two different layouts which are recommended only as guidelines. Other suitable clock layouts may exist and it would be recommended that the board designers simulate to guarantee compatibility across all printed circuit and clock component process variations.

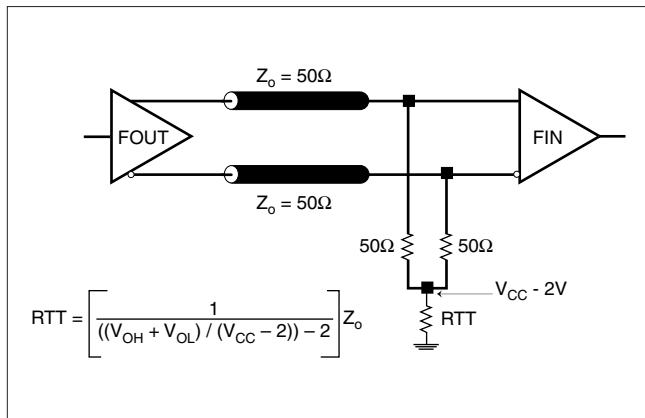


FIGURE 3A. LVPECL OUTPUT TERMINATION

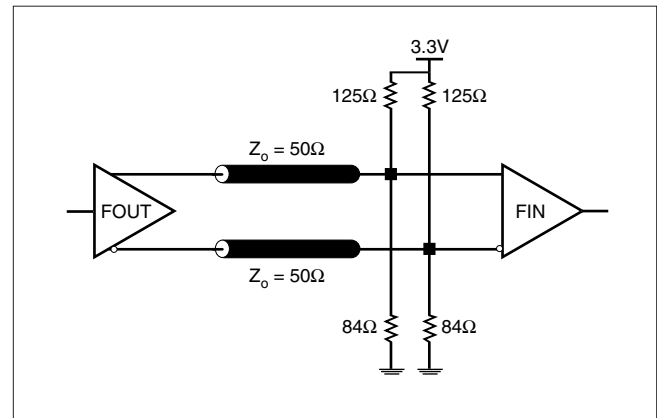


FIGURE 3B. LVPECL OUTPUT TERMINATION

Figure 4A and Figure 4B show examples of termination for 2.5V LVPECL driver. These terminations are equivalent to terminating 50Ω to $V_{cc} - 2V$. For $V_{cc} = 2.5V$, the $V_{cc} - 2V$ is very close to ground

The diagram shows a differential signal driver circuit. On the left, a triangle symbol represents the '2.5V LVPECL Driver'. Its output is connected to two parallel horizontal lines, each labeled 'Zo = 50 Ohm'. These lines connect to a central node. This node is also connected to a 2.5V supply (top) and a ground symbol (bottom). The central node is connected to a differential pair of inputs (marked '+' and '-') of another 2.5V supply. The circuit is labeled '2.5V' at the top and bottom.

IDT™ / ICS™ 3.3V, 2.5V LVPECL CLOCK GENERATOR

POWER CONSIDERATIONS

This section provides information on power dissipation and junction temperature for the ICS843023I. Equations and example calculations are also provided.

1. Power Dissipation.

The total power dissipation for the ICS843023I is the sum of the core power plus the power dissipated in the load(s). The following is the power dissipation for $V_{CC} = 3.3V + 5\% = 3.465V$, which gives worst case results.

NOTE: Please refer to Section 3 for details on calculating power dissipated in the load.

- Power (core)_{MAX} = $V_{CC_MAX} * I_{EE_MAX} = 3.465V * 75mA = 259.87mW$
- Power (outputs)_{MAX} = **30mW/Loaded Output pair**

$$\text{Total Power}_{MAX} (3.465V, \text{ with all outputs switching}) = 259.87mW + 30mW = 389.87mW$$

2. Junction Temperature.

Junction temperature, T_j , is the temperature at the junction of the bond wire and bond pad and directly affects the reliability of the device. The maximum recommended junction temperature for HiPerClockS™ devices is 125°C.

The equation for T_j is as follows: $T_j = \theta_{JA} * Pd_total + T_A$

T_j = Junction Temperature

θ_{JA} = Junction-to-Ambient Thermal Resistance

Pd_total = Total Device Power Dissipation (example calculation is in section 1 above)

T_A = Ambient Temperature

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance θ_{JA} must be used. Assuming a moderate air flow of 1 meter per second and a multi-layer board, the appropriate value is 90.5°C/W per Table 6 below.

Therefore, T_j for an ambient temperature of 85°C with all outputs switching is:

$$85^\circ C + 0.290W * 90.5^\circ C/W = 111.2^\circ C. \text{ This is below the limit of } 125^\circ C.$$

This calculation is only an example. T_j will obviously vary depending on the number of loaded outputs, supply voltage, air flow, and the type of board (single layer or multi-layer).

TABLE 6. THERMAL RESISTANCE θ_{JA} FOR 8-PIN TSSOP, FORCED CONVECTION

θ_{JA} by Velocity (Meters per Second)			
	0	1	2.5
Multi-Layer PCB, JEDEC Standard Test Boards	101.7°C/W	90.5°C/W	89.8°C/W

3. Calculations and Equations.

The purpose of this section is to derive the power dissipated into the load.

LVPECL output driver circuit and termination are shown in *Figure 5*.

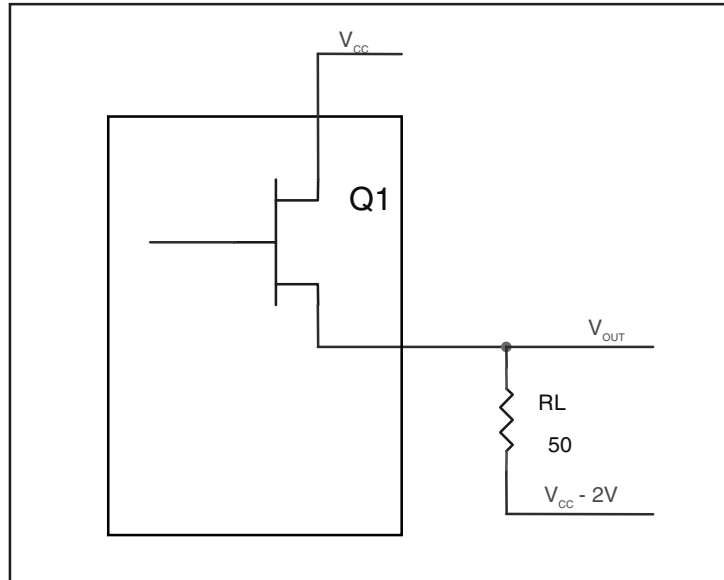


FIGURE 5. LVPECL DRIVER CIRCUIT AND TERMINATION

To calculate worst case power dissipation into the load, use the following equations which assume a 50Ω load, and a termination voltage of $V_{CC} - 2V$.

- For logic high, $V_{OUT} = V_{OH_MAX} = V_{CC_MAX} - 0.9V$

$$(V_{CC_MAX} - V_{OH_MAX}) = 0.9V$$

- For logic low, $V_{OUT} = V_{OL_MAX} = V_{CC_MAX} - 1.7V$

$$(V_{CC_MAX} - V_{OL_MAX}) = 1.7V$$

Pd_H is power dissipation when the output drives high.

Pd_L is the power dissipation when the output drives low.

$$Pd_H = [(V_{OH_MAX} - (V_{CC_MAX} - 2V))/R_L] * (V_{CC_MAX} - V_{OH_MAX}) = [(2V - (V_{CC_MAX} - V_{OH_MAX}))/R_L] * (V_{CC_MAX} - V_{OH_MAX}) = [(2V - 0.9V)/50\Omega] * 0.9V = 19.8mW$$

$$Pd_L = [(V_{OL_MAX} - (V_{CC_MAX} - 2V))/R_L] * (V_{CC_MAX} - V_{OL_MAX}) = [(2V - (V_{CC_MAX} - V_{OL_MAX}))/R_L] * (V_{CC_MAX} - V_{OL_MAX}) = [(2V - 1.7V)/50\Omega] * 1.7V = 10.2mW$$

$$\text{Total Power Dissipation per output pair} = Pd_H + Pd_L = 30mW$$

RELIABILITY INFORMATION

TABLE 7. θ_{JA} VS. AIR FLOW TABLE FOR 8 LEAD TSSOP

θ_{JA} by Velocity (Meters per Second)			
	0	1	2.5
Multi-Layer PCB, JEDEC Standard Test Boards	101.7°C/W	90.5°C/W	89.8°C/W

TRANSISTOR COUNT

The transistor count for ICS843023I is: 2360

PACKAGE OUTLINE - G SUFFIX FOR 8 LEAD TSSOP

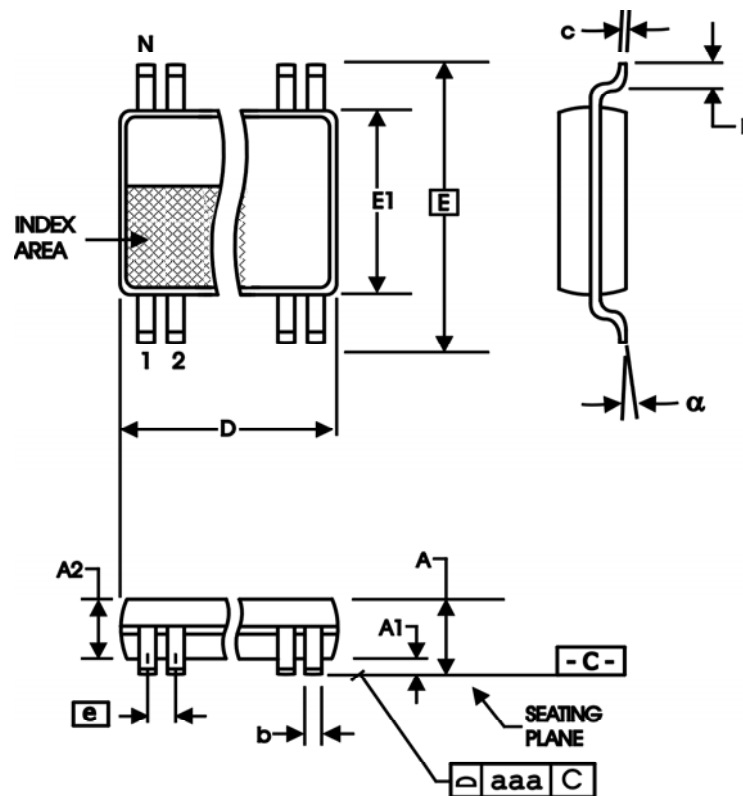


TABLE 8. PACKAGE DIMENSIONS

SYMBOL	Millimeters	
	Minimum	Maximum
N	8	
A	--	1.20
A1	0.05	0.15
A2	0.80	1.05
b	0.19	0.30
c	0.09	0.20
D	2.90	3.10
E	6.40 BASIC	
E1	4.30	4.50
e	0.65 BASIC	
L	0.45	0.75
α	0°	8°
aaa	--	0.10

Reference Document: JEDEC Publication 95, MO-153

TABLE 9. ORDERING INFORMATION

Part/Order Number	Marking	Package	Shipping Packaging	Temperature
ICS843023AGI	023AI	8 Lead TSSOP	tube	-40°C to 85°C
ICS843023AGIT	023AI	8 Lead TSSOP	2500 tape & reel	-40°C to 85°C
ICS843023AGILF	TBD	8 Lead "Lead-Free" TSSOP	tube	-40°C to 85°C
ICS843023AGILFT	TBD	8 Lead "Lead-Free" TSSOP	2500 tape & reel	-40°C to 85°C

NOTE: Parts that are ordered with an "LF" suffix to the part number are the Pb-Free configuration and are RoHS compliant.

While the information presented herein has been checked for both accuracy and reliability, Integrated Device Technology, Incorporated (IDT) assumes no responsibility for either its use or for infringement of any patents or other rights of third parties, which would result from its use. No other circuits, patents, or licenses are implied. This product is intended for use in normal commercial and industrial applications. Any other applications such as those requiring high reliability or other extraordinary environmental requirements are not recommended without additional processing by IDT. IDT reserves the right to change any circuitry or specifications without notice. IDT does not authorize or warrant any IDT product for use in life support devices or critical medical instruments.

REVISION HISTORY SHEET

Rev	Table	Page	Description of Change	Date
B	T4 T5A & T5B	1	Features Section - changed minimum output frequency range from 245MHz to 240MHz. Changed minimum VCO range from 490MHz to 480MHz.	1/9/07
		4	Crystal Characteristics Table - changed minimum frequency from 24.5MHz to 24MHz.	
		4	AC Characteristics Tables - changed minimum output frequency from 245MHz to 240MHz.	
		7	Added LVCMOS to XTAL Interface section.	

Innovate with IDT and accelerate your future networks. Contact:

www.IDT.com

For Sales

800-345-7015
408-284-8200
Fax: 408-284-2775

For Tech Support

netcom@idt.com
480-763-2056

Corporate Headquarters

Integrated Device Technology, Inc.
6024 Silver Creek Valley Road
San Jose, CA 95138
United States
800 345 7015
+408 284 8200 (outside U.S.)

Asia Pacific and Japan

Integrated Device Technology
Singapore (1997) Pte. Ltd.
Reg. No. 199707558G
435 Orchard Road
#20-03 Wisma Atria
Singapore 238877
+65 6 887 5505

Europe

IDT Europe, Limited
321 Kingston Road
Leatherhead, Surrey
KT22 7TU
England
+44 (0) 1372 363 339
Fax: +44 (0) 1372 378851